

Piotr Perlin

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

200
papers

3,605
citations

27
h-index

54
g-index

258
ext. papers

3,995
ext. citations

2.4
avg, IF

4.55
L-index

#	Paper	IF	Citations
200	Influence of the a-directed off-cut on the opto-electrical properties of laser diodes grown on the 0.3° misoriented m-directed GaN substrate. <i>Optical Materials Express</i> , 2022 , 12, 991	2.6	0
199	GaN Laser Diode Technology for Visible-Light Communications. <i>Electronics (Switzerland)</i> , 2022 , 11, 1430	2.6	1
198	Refractive Index of Heavily Germanium-Doped Gallium Nitride Measured by Spectral Reflectometry and Ellipsometry. <i>Materials</i> , 2021 , 14,	3.5	2
197	Homoepitaxial ZnO/ZnMgO Laser Structures and Their Properties. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2000344	1.6	0
196	Effects of MOVPE Growth Conditions on GaN Layers Doped with Germanium. <i>Materials</i> , 2021 , 14,	3.5	3
195	Dynamic Device Characteristics and Linewidth Measurement of InGaN/GaN Laser Diodes. <i>IEEE Photonics Journal</i> , 2021 , 13, 1-10	1.8	2
194	Role of dislocations in nitride laser diodes with different indium content. <i>Scientific Reports</i> , 2021 , 11, 21	4.9	4
193	Surface Photochemical Corrosion as a Mechanism for Fast Degradation of InGaN UV Laser Diodes. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 52089-52094	9.5	2
192	Highly stable GaN-based betavoltaic structures grown on different dislocation density substrates. <i>Solid-State Electronics</i> , 2020 , 167, 107784	1.7	2
191	Kinetics of the radiative and nonradiative recombination in polar and semipolar InGaN quantum wells. <i>Scientific Reports</i> , 2020 , 10, 1235	4.9	1
190	InGaN blue light emitting micro-diodes with current path defined by tunnel junction. <i>Optics Letters</i> , 2020 , 45, 4332-4335	3	1
189	Review on Optimization and Current Status of (Al,In)GaN Superluminescent Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 015010	2	6
188	Edge Emitting Laser Diodes and Superluminescent Diodes 2020 , 333-365		
187	GaN-based distributed feedback laser diodes for optical communications 2019 ,		2
186	Material Issues in GaN-based Laser Diode Manufacturing 2019 ,		1
185	Recent progress in distributed feedback InGaN/GaN laser diodes 2019 ,		1
184	Screening of quantum-confined Stark effect in nitride laser diodes and superluminescent diodes. <i>Applied Physics Express</i> , 2019 , 12, 044001	2.4	7

183	Extremely long lifetime of III-nitride laser diodes grown by plasma assisted molecular beam epitaxy. <i>Materials Science in Semiconductor Processing</i> , 2019 , 91, 387-391	4.3	9
182	Hydrogen diffusion in GaN:Mg and GaN:Si. <i>Journal of Alloys and Compounds</i> , 2018 , 747, 354-358	5.7	18
181	Direct evidence of photoluminescence broadening enhancement by local electric field fluctuations in polar InGaN/GaN quantum wells. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 020305	1.4	3
180	Role of the electron blocking layer in the graded-index separate confinement heterostructure nitride laser diodes. <i>Superlattices and Microstructures</i> , 2018 , 116, 114-121	2.8	2
179	450 nm (Al,In)GaN optical amplifier with double 'j-shape' waveguide for master oscillator power amplifier systems. <i>Optics Express</i> , 2018 , 26, 7351-7357	3.3	10
178	InAlGaIn superluminescent diodes fabricated on patterned substrates: an alternative semiconductor broadband emitter: publisher's note. <i>Photonics Research</i> , 2018 , 6, 652	6	3
177	Impact of dislocations on DLTS spectra and degradation of InGaIn-based laser diodes. <i>Microelectronics Reliability</i> , 2018 , 88-90, 864-867	1.2	4
176	Continuous-wave operation of (Al,In)GaN distributed-feedback laser diodes with high-order notched gratings. <i>Applied Physics Express</i> , 2018 , 11, 112701	2.4	19
175	Switching of exciton character in double InGaIn/GaN quantum wells. <i>Physical Review B</i> , 2018 , 98,	3.3	8
174	True-blue laser diodes with tunnel junctions grown monolithically by plasma-assisted molecular beam epitaxy. <i>Applied Physics Express</i> , 2018 , 11, 034103	2.4	34
173	Influence of hydrogen pre-growth flow on indium incorporation into InGaIn layers. <i>Journal of Crystal Growth</i> , 2017 , 464, 123-126	1.6	2
172	Impact of thermal crosstalk between emitters on power roll-over in nitride-based blue-violet laser bars. <i>Semiconductor Science and Technology</i> , 2017 , 32, 025008	1.8	0
171	AlGaInN laser-diode technology for optical clocks and atom interferometry 2017 ,		4
170	Lateral grating DFB AlGaInN laser diodes for optical communications and atomic clocks.. <i>Journal of Physics: Conference Series</i> , 2017 , 810, 012053	0.3	1
169	High-resolution mirror temperature mapping in GaN-based diode lasers by thermoreflectance spectroscopy. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 020302	1.4	5
168	Long-term degradation of InGaIn-based laser diodes: Role of defects. <i>Microelectronics Reliability</i> , 2017 , 76-77, 584-587	1.2	1
167	Examination of thermal properties and degradation of InGaIn - based diode lasers by thermoreflectance spectroscopy and focused ion beam etching. <i>AIP Advances</i> , 2017 , 7, 075107	1.5	4
166	Influence of the growth method on degradation of InGaIn laser diodes. <i>Applied Physics Express</i> , 2017 , 10, 091001	2.4	8

165	AlGaInN diode-laser technology for optical clocks and atom interferometry. <i>Journal of Physics: Conference Series</i> , 2017 , 810, 012052	0.3	1
164	Aluminum-free nitride laser diodes: waveguiding, electrical and degradation properties. <i>Optics Express</i> , 2017 , 25, 33113	3.3	5
163	InAlGaInN superluminescent diodes fabricated on patterned substrates: an alternative semiconductor broadband emitter. <i>Photonics Research</i> , 2017 , 5, A30	6	12
162	AlGaInN laser diode bars for high-power, optical integration and quantum technologies 2017 ,		1
161	GaN laser diodes for quantum technologies 2017 ,		1
160	Tapered waveguide high power AlGaInN laser diodes and amplifiers for optical integration and quantum technologies 2017 ,		2
159	Elimination of leakage of optical modes to GaN substrate in nitride laser diodes using a thick InGaInN waveguide. <i>Applied Physics Express</i> , 2016 , 9, 092103	2.4	21
158	High speed visible light communication using blue GaN laser diodes 2016 ,		6
157	Free-space and underwater GHz data transmission using AlGaInN laser diode technology 2016 ,		2
156	Suppression of extended defects propagation in a laser diodes structure grown on (20-21) GaN. <i>Semiconductor Science and Technology</i> , 2016 , 31, 035001	1.8	6
155	AlGaInN laser diode technology for GHz high-speed visible light communication through plastic optical fiber and water. <i>Optical Engineering</i> , 2016 , 55, 026112	1.1	14
154	AlGaInN laser diode technology for systems applications 2016 ,		2
153	Development of the Nitride Laser Diode Arrays for Video and Movie Projectors. <i>MRS Advances</i> , 2016 , 1, 103-108	0.7	5
152	Nitride superluminescent diodes with broadened emission spectrum fabricated using laterally patterned substrate. <i>Optics Express</i> , 2016 , 24, 9673-82	3.3	17
151	Photo-etching of GaN: Revealing nano-scale non-homogeneities. <i>Journal of Crystal Growth</i> , 2015 , 426, 153-158	1.6	9
150	Properties of InGaInN/GaN multiquantum wells grown on semipolar (20-21) substrates with different miscuts. <i>Journal of Crystal Growth</i> , 2015 , 423, 28-33	1.6	2
149	Advances in single mode and high power AlGaInN laser diode technology for systems applications 2015 ,		2
148	Negative-T0 InGaInN laser diodes and their degradation. <i>Applied Physics Letters</i> , 2015 , 106, 171107	3.4	7

147	High power nitride laser diodes grown by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2015 , 425, 398-400	1.6	13
146	Integrated RGB laser light module for autostereoscopic outdoor displays 2015 ,		4
145	Design and optimization of InGaN superluminescent diodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 997-1004	1.6	14
144	Enhancement of optical confinement factor by InGaN waveguide in blue laser diodes grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Express</i> , 2015 , 8, 032103	2.4	23
143	A multi-wavelength (u.v. to visible) laser system for early detection of oral cancer 2015 ,		4
142	. <i>IEEE Sensors Journal</i> , 2015 , 15, 123-127	4	3
141	Numerical investigation of an impact of a top gold metallization on output power of a p-up III-N-based blue-violet edge-emitting laser diode. <i>Opto-electronics Review</i> , 2015 , 23,	2.4	2
140	Thermal conductivity of donor-doped GaN measured with 3 μ m and stationary methods. <i>Low Temperature Physics</i> , 2015 , 41, 563-566	0.7	1
139	Effect of hydrogen during growth of quantum barriers on the properties of InGaN quantum wells. <i>Journal of Crystal Growth</i> , 2015 , 414, 38-41	1.6	20
138	True-blue laser diodes grown by plasma-assisted MBE on bulk GaN substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 666-669		1
137	Influence of hydrogen and TMIn on indium incorporation in MOVPE growth of InGaN layers. <i>Journal of Crystal Growth</i> , 2014 , 402, 330-336	1.6	19
136	Semipolar (202 μ m) GaN laser diodes operating at 388 nm grown by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 02C115	1.3	1
135	Optical optimization of InGaN/GaN edge-emitting lasers with reduced AlGaIn cladding thickness. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 032701	1.4	5
134	Cavity-Free Lasing and 2D Plasma Oscillations in Optically Excited InGaN Heterostructures. <i>Journal of Russian Laser Research</i> , 2014 , 35, 447-456	0.7	2
133	AlGaIn cladding-free 482 nm continuous wave nitride laser diodes grown by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 02C112	1.3	
132	Cyan laser diode grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2014 , 104, 023503	3.4	8
131	AlGaInN laser diode technology for defence, security and sensing applications 2014 ,		7
130	Assessment of laser tracking and data transfer for underwater optical communications 2014 ,		4

129	Nitride-based laser diodes and superluminescent diodes. <i>Photonics Letters of Poland</i> , 2014 , 6,	2.1	2
128	Determination of gain in AlGaIn cladding free nitride laser diodes. <i>Applied Physics Letters</i> , 2013 , 103, 061102	3.4	12
127	Emission wavelength dependence of characteristic temperature of InGaIn laser diodes. <i>Applied Physics Letters</i> , 2013 , 103, 071102	3.4	9
126	InGaIn laser diodes with reduced AlGaIn cladding thickness fabricated on GaIn plasmonic substrate. <i>Applied Physics Letters</i> , 2013 , 102, 151102	3.4	11
125	High optical power ultraviolet superluminescent InGaIn diodes 2013 ,		2
124	Ultraviolet laser diodes grown on semipolar (202̄1) GaIn substrates by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 251101	3.4	12
123	MBE fabrication of III-N-based laser diodes and its development to industrial system. <i>Journal of Crystal Growth</i> , 2013 , 378, 278-282	1.6	13
122	Visible light communications using a directly modulated 422 nm GaIn laser diode. <i>Optics Letters</i> , 2013 , 38, 3792-4	3	86
121	Graded-index separate confinement heterostructure InGaIn laser diodes. <i>Applied Physics Letters</i> , 2013 , 103, 261107	3.4	24
120	High-Optical-Power InGaIn Superluminescent Diodes with U-shape Waveguide. <i>Applied Physics Express</i> , 2013 , 6, 092102	2.4	25
119	InGaIn Laser Diode Degradation 2013 , 247-261		1
118	Universal behavior of photoluminescence in GaIn-based quantum wells under hydrostatic pressure governed by built-in electric field. <i>Journal of Applied Physics</i> , 2012 , 112, 053509	2.5	13
117	GaIn substrates with variable vicinal angles for laser diode applications 2012 ,		2
116	Highly doped GaIn: a material for plasmonic claddings for blue/green InGaIn laser diodes 2012 ,		10
115	Electronic tuning of integrated blue-violet GaIn tunable coupled-cavity laser. <i>AIP Advances</i> , 2012 , 2, 032139		10
114	Unambiguous relationship between photoluminescence energy and its pressure evolution in InGaIn/GaIn quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , 2012 , 249, 476-479	1.3	1
113	InGaIn tapered laser diodes. <i>Electronics Letters</i> , 2012 , 48, 1232	1.1	3
112	True-Blue Nitride Laser Diodes Grown by Plasma-Assisted Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2012 , 5, 112103	2.4	16

111	AlGaIn-Free Laser Diodes by Plasma-Assisted Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2012 , 5, 022104	2.4	15
110	Lateral Control of Indium Content and Wavelength of III-Nitride Diode Lasers by Means of GaN Substrate Patterning. <i>Applied Physics Express</i> , 2012 , 5, 021001	2.4	21
109	InGaIn laser diodes operating at 450-460 nm grown by rf-plasma MBE. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 02B102	1.3	15
108	Cavity suppression in nitride based superluminescent diodes. <i>Journal of Applied Physics</i> , 2012 , 111, 083105	1.5	27
107	Waveguide Design for Long Wavelength InGaIn Based Laser Diodes. <i>Acta Physica Polonica A</i> , 2012 , 122, 1031-1033	0.6	7
106	Optically pumped 500 nm InGaIn green lasers grown by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2011 , 110, 063110	2.5	39
105	Different behavior of semipolar and polar InGaIn/GaN quantum wells: Pressure studies of photoluminescence. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 1526-1528	1.6	3
104	Indium incorporation into InGaIn and InAlIn layers grown by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , 2011 , 318, 496-499	1.6	32
103	InGaIn mini-laser diode arrays with cw output power of 500 mW. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2348-2350		2
102	Secondary ions mass spectroscopy measurements of dopant impurities in highly stressed InGaIn laser diodes. <i>Applied Physics Letters</i> , 2011 , 98, 241115	3.4	12
101	InGaIn Laser Diode Mini-Arrays. <i>Applied Physics Express</i> , 2011 , 4, 062103	2.4	20
100	Thin Film ZnO as Sublayer for Electric Contact for Bulk GaIn with Low Electron Concentration. <i>Acta Physica Polonica A</i> , 2011 , 119, 672-674	0.6	5
99	InAlGaIn laser diodes grown by plasma assisted molecular beam epitaxy. <i>Lithuanian Journal of Physics</i> , 2011 , 51, 276-282	1.1	0
98	Interplay between Internal and External Electric Field Studied by Photoluminescence in InGaIn/GaN Light Emitting Diodes. <i>Acta Physica Polonica A</i> , 2011 , 120, 891-893	0.6	
97	Hole carrier concentration and photoluminescence in magnesium doped InGaIn and GaIn grown on sapphire and GaIn misoriented substrates. <i>Journal of Applied Physics</i> , 2010 , 108, 023516	2.5	14
96	Temperature dependence of superluminescence in InGaIn-based superluminescent light emitting diode structures. <i>Journal of Applied Physics</i> , 2010 , 108, 013110	2.5	17
95	Tilt of InGaIn layers on miscut GaIn substrates. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010 , 4, 142-144	1.4	9
94	. <i>Proceedings of the IEEE</i> , 2010 , 98, 1214-1219	14.3	15

93	NiAu contacts to p-type GaN structure and properties. <i>Solid-State Electronics</i> , 2010 , 54, 701-709	1.7	25
92	Interplay of stimulated emission and Auger-like effect in violet and blue InGaN laser diodes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 1835-1837		
91	Application of a composite plasmonic substrate for the suppression of an electromagnetic mode leakage in InGaN laser diodes. <i>Applied Physics Letters</i> , 2009 , 95, 261108	3.4	24
90	Effect of efficiency droop in violet and blue InGaN laser diodes. <i>Applied Physics Letters</i> , 2009 , 95, 071108	3.4	19
89	InGaN Laser Diode Degradation. Surface and Bulk Processes. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1195, 52		2
88	Nitride-based quantum structures and devices on modified GaN substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1130-1134	1.6	15
87	Violet blue laser mini-bars. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S837-S839		4
86	What is new in nitride laser diodes reliability studies. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S881-S884		
85	New approach to cathodoluminescence studies in application to InGaN/GaN laser diode degradation. <i>Journal of Microscopy</i> , 2009 , 236, 137-42	1.9	3
84	Nitride laser diode arrays 2009 ,		2
83	Why InGaN laser-diode degradation is accompanied by the improvement of its thermal stability 2008 ,		7
82	Carrier recombination mechanisms in nitride single quantum well light-emitting diodes revealed by photo- and electroluminescence. <i>Journal of Applied Physics</i> , 2008 , 104, 094504	2.5	3
81	Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2008 , 93, 172117	3.4	26
80	Optically pumped lasing of GaN/AlGaN structures grown along a non-polar crystallographic direction. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 2173-2175		
79	Fabrication and properties of GaN-based lasers. <i>Journal of Crystal Growth</i> , 2008 , 310, 3979-3982	1.6	10
78	Thermal analysis of InGaN/GaN (GaN substrate) laser diodes using transient interferometric mapping. <i>Microelectronics Reliability</i> , 2007 , 47, 1649-1652	1.2	1
77	Bulk GaN crystal growth by the high-pressure ammonothermal method. <i>Journal of Crystal Growth</i> , 2007 , 300, 11-16	1.6	63
76	Role of dislocation-free GaN substrates in the growth of indium containing optoelectronic structures by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , 2007 , 305, 346-354	1.6	18

75	Optical gain and saturation behavior in homoepitaxially grown InGaN/GaN/AlGaIn laser structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 82-85		
74	Micro-analysis of light emission properties of GaN-based laser diodes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2818-2821		
73	Capture kinetics at deep-level electron traps in GaN-based laser diode. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 2878-2882		6
72	Investigation of polarization-induced electric field screening in InGaN light emitting diodes by means of hydrostatic pressure. <i>Physica Status Solidi (B): Basic Research</i> , 2007 , 244, 32-37	1.3	3
71	Comparison of gain in group-III-nitride laser structures grown by metalorganic vapour phase epitaxy and plasma-assisted molecular beam epitaxy on bulk GaN substrates. <i>Semiconductor Science and Technology</i> , 2007 , 22, 736-741	1.8	3
70	Optically pumped GaN/AlGaIn separate-confinement heterostructure laser grown along the (1120) nonpolar direction. <i>Applied Physics Letters</i> , 2007 , 90, 081104	3.4	14
69	Nitride based laser diodes on substrates with patterned AlN mask. <i>Applied Physics Letters</i> , 2007 , 91, 221103	3.03	4
68	Role of the electron blocking layer in the low-temperature collapse of electroluminescence in nitride light-emitting diodes. <i>Applied Physics Letters</i> , 2007 , 90, 103507	3.4	44
67	Correlation between luminescence and compositional striations in InGaIn layers grown on miscut GaN substrates. <i>Applied Physics Letters</i> , 2007 , 91, 211904	3.4	35
66	Mode dynamics of high power (InAl)GaIn based laser diodes grown on bulk GaIn substrate. <i>Journal of Applied Physics</i> , 2007 , 101, 083109	2.5	12
65	Deep-Level Defects in MBE-Grown GaIn-Based Laser Structure. <i>Acta Physica Polonica A</i> , 2007 , 112, 331-337	3.76	2
64	Optically Pumped Laser Action on Nitride Based Separate Confinement Heterostructures Grown along the (1120) Crystallographic Direction. <i>Acta Physica Polonica A</i> , 2007 , 112, 467-472	0.6	
63	Elimination of AlGaIn epilayer cracking by spatially patterned AlN mask. <i>Applied Physics Letters</i> , 2006 , 88, 121124	3.4	22
62	Strong electric field and nonuniformity effects in GaN/AlN quantum dots revealed by high pressure studies. <i>Applied Physics Letters</i> , 2006 , 89, 051902	3.4	6
61	60mW continuous-wave operation of InGaIn laser diodes made by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2006 , 88, 221108	3.4	45
60	Degradation mechanisms in InGaIn laser diodes grown on bulk GaIn crystals. <i>Applied Physics Letters</i> , 2006 , 88, 201111	3.4	64
59	Band-to-band character of photoluminescence from InN and In-rich InGaIn revealed by hydrostatic pressure studies. <i>Applied Physics Letters</i> , 2006 , 89, 121915	3.4	13
58	Anomalous temperature characteristics of single wide quantum well InGaIn laser diode. <i>Applied Physics Letters</i> , 2006 , 88, 071121	3.4	19

57	Hydrostatic pressure dependence of polarization-induced interface charge in AlGaIn/GaN heterostructures determined by means of capacitance-voltage characterization. <i>Journal of Applied Physics</i> , 2006 , 100, 113712	2.5	4
56	Broad-area high-power CW operated InGaN laser diodes 2006 , 6133, 168		5
55	High-Pressure Crystallization of GaN 2006 , 1-43		
54	Screening of polarization induced electric fields in blue/violet InGaIn/GaN laser diodes by Si doping in quantum barriers revealed by hydrostatic pressure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 2303-2306		3
53	Profiling of light emission of GaN-based laser diodes with cathodoluminescence. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 1811-1814	1.6	1
52	Towards identification of degradation mechanisms in InGaIn laser diodes grown on bulk GaN crystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 1778-1782	1.6	4
51	Role of band potential roughness on the luminescence properties of InGaIn quantum wells grown by MBE on bulk GaN substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1614-1618	1.3	6
50	High Power Continuous Wave Blue InAlGaIn Laser Diodes Made by Plasma Assisted MBE. <i>Acta Physica Polonica A</i> , 2006 , 110, 345-351	0.6	1
49	High power blue-violet InGaIn laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 2005 , 20, 809-813	1.8	30
48	Fully-screened polarization-induced electric fields in blue-violet InGaIn/GaN light-emitting devices grown on bulk GaN. <i>Applied Physics Letters</i> , 2005 , 87, 041109	3.4	37
47	Properties of violet laser diodes grown on bulk GaN substrates 2005 ,		4
46	Properties of InGaIn blue laser diodes grown on bulk GaN substrates. <i>Journal of Crystal Growth</i> , 2005 , 281, 107-114	1.6	6
45	Spontaneous and stimulated emission in quantum structures grown over bulk GaN and sapphire. <i>Journal of Crystal Growth</i> , 2005 , 281, 183-187	1.6	2
44	Surface and electronic structure of Ga _{0.92} In _{0.08} N thin film investigated by photoelectron spectroscopy. <i>Thin Solid Films</i> , 2005 , 476, 396-404	2.2	1
43	Screening of built-in electric fields in group III-nitride laser diodes observed by means of hydrostatic pressure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1019-1022		1
42	Localization Effects in InGaIn/GaN Double Heterostructure Laser Diode Structures Grown on Bulk GaN Crystals. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 7244-7249	1.4	2
41	Efficient radiative recombination and potential profile fluctuations in low-dislocation InGaIn/GaN multiple quantum wells on bulk GaN substrates. <i>Journal of Applied Physics</i> , 2005 , 97, 103507	2.5	20
40	Blue-violet InGaIn laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2005 , 86, 011114	3.4	62

39	Free and bound excitons in GaN/AlGaIn homoepitaxial quantum wells grown on bulk GaN substrate along the nonpolar (1120) direction. <i>Applied Physics Letters</i> , 2005 , 86, 162112	3.4	25
38	Stimulated Emission from the MBE Grown Homoepitaxial InGaIn Based Multiple Quantum Wells Structures. <i>Acta Physica Polonica A</i> , 2005 , 107, 225-229	0.6	
37	Low dislocation density, high power InGaIn laser diodes. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 2004 , 9, 1		9
36	High-power laser structures grown on bulk GaN crystals. <i>Journal of Crystal Growth</i> , 2004 , 272, 274-277	1.6	9
35	Observation of localization effects in InGaIn/GaN quantum structures by means of the application of hydrostatic pressure. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 3285-3292	1.3	5
34	Nonlinear optical characterization of single-crystalline GaN by Z-scan technique 2001 ,		1
33	Luminescence of nonthermalized electron-hole plasma in GaN epilayers 2001 ,		1
32	Light emitters fabricated on bulk GaN substrates. Challenges and achievements.. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 693, 561		
31	The effects of indium concentration and well-thickness on the mechanisms of radiative recombination in In _x Ga _{1-x} N quantum wells. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 2000 , 5, 1		46
30	GaN thin films by growth on Ga-rich GaN buffer layers. <i>Journal of Applied Physics</i> , 2000 , 88, 6032-6036	2.5	17
29	Interband optical absorption in free standing layer of Ga _{0.96} In _{0.04} As _{0.99} N _{0.01} . <i>Applied Physics Letters</i> , 2000 , 76, 1279-1281	3.4	62
28	Growth of 1.3 μm InGaAsN laser material on GaAs by molecular beam epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999 , 17, 1272		48
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